

Epitaxial Thin Film Growth of Perovskite Hydrides $M\text{LiH}_3$ (M : Sr, Ba) for The Study of Intrinsic Hydride-Ion Conduction

Erika Fukushi¹, Fumiya Mori¹, Kota Munefusa¹, Takayuki Harada² and Hiroyuki Oguchi^{1*}

¹Department of Applied Chemistry, Graduate School of Engineering and Science, Shibaura Institute of Technology, 3-7-5 Toyosu, Koto-ku, Tokyo, Japan

²Research Center for Materials Nanoarchitectonics (MANA), National Institute for Materials Science, 1-1 Namiki, Tsukuba-shi, Ibaraki, Japan

*E-mail: h-oguchi@shibaura-it.ac.jp

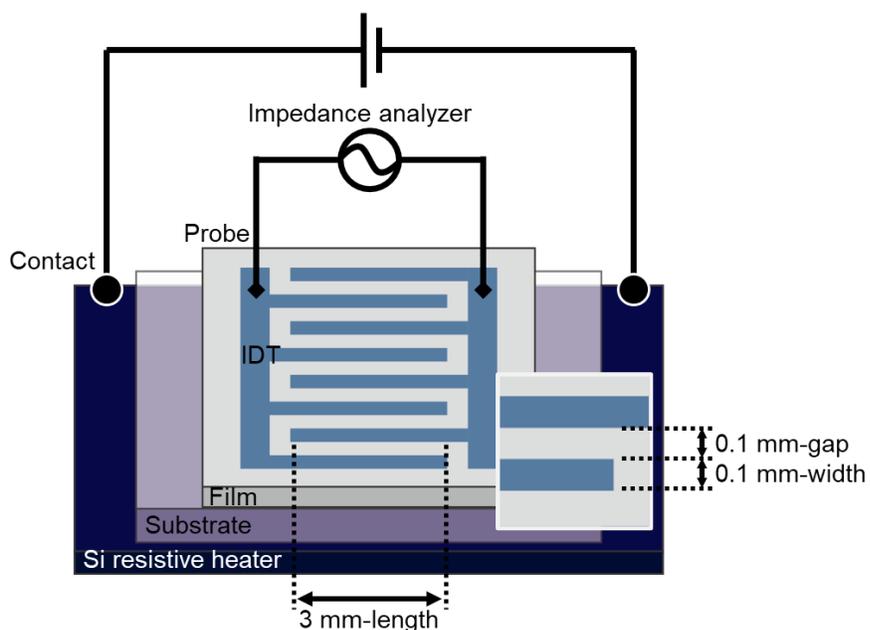


Figure S1. Schematic of the in-plane ionic conductivity measurement setup: Mo comb-shaped electrode consists of about 10 parallel teeth (the number of teeth was varied depending on the sample size), each with an overlap length of 3 mm and a width and spacing of 0.1 mm. To heat the film, a Si plate (conductivity: 0.01-0.02 Ωcm) placed at the bottom of the substrate was used as a resistance heater. Assuming temperature equilibrium between the Si plate and the sample, the sample temperature was determined by measuring the temperature of the Si plate using a radiation thermometer (TMHX-TME0050(H), Nihon Sensor Co.)

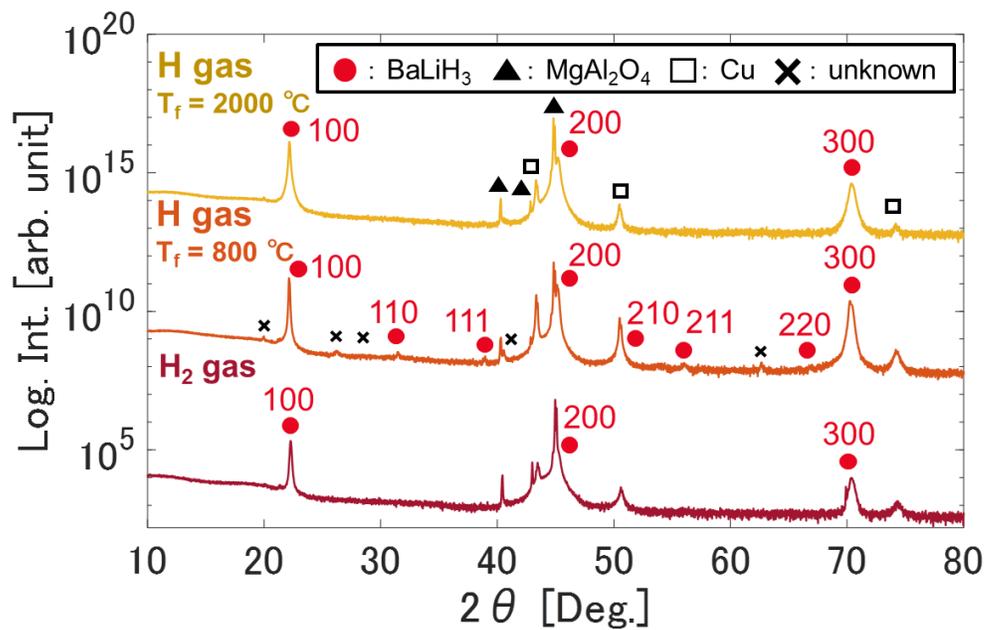


Figure S2. $2\theta/\theta$ XRD diffraction patterns of BaLiH₃ thin films with different reaction gases. Diffraction peaks attributed to BaLiH₃ appear in all gas conditions.

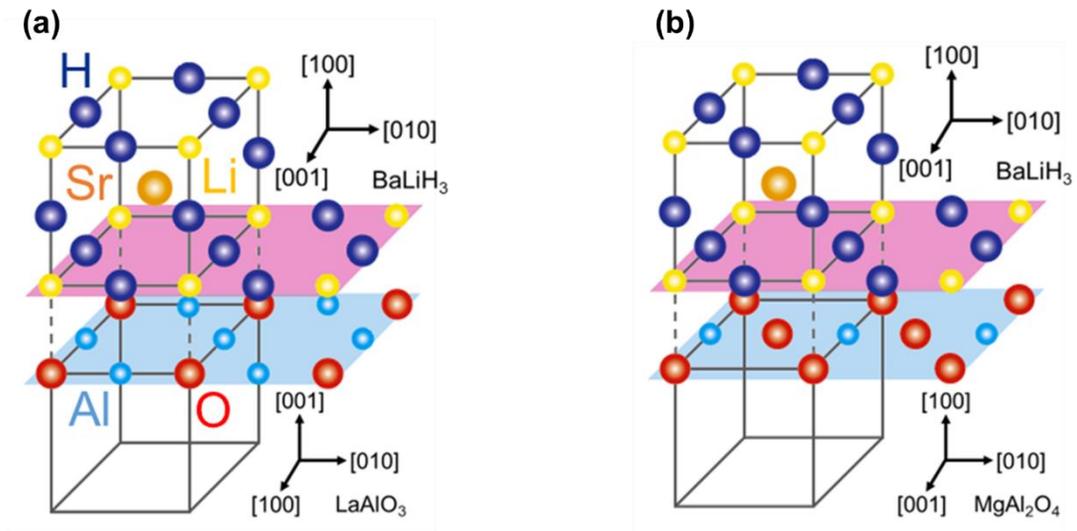


Figure S3. Atomic arrangement of the epitaxial thin film on (a) MgAl₂O₄ and (b) LaAlO₃ substrate as predicted from the XRD diffraction pattern shown in Figure 6.

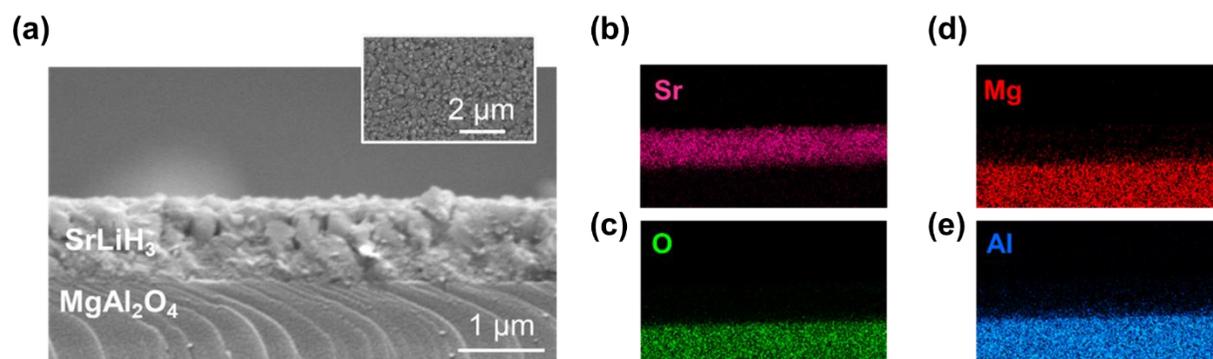


Figure S4. (a) SEM cross section of SrLiH₃ epitaxial thin film grown on MgAl₂O₄ substrate and EDS mapping for (b) Sr, (c) O, (d) Mg, and (e) Al elements. Inset shows surface SEM image.